

ABSTRACT OF THE DISCLOSURE

The present invention provides a semiconductor device having a power transistor of low ON resistance. The semiconductor device includes a metal-made header, a semiconductor chip which is fixed to the header and constitutes a MOSFET, and a sealing body made of insulating resin which covers the semiconductor chip, the header and the like. The semiconductor device further includes a drain lead which is contiguously formed with the header and projects from one side surface of the sealing body, and a source lead and a gate lead which project in parallel from one side surface of the sealing body, and wires which are positioned in the inside of the sealing body and connect electrodes on an upper surface of the semiconductor chip and source lead and the gate lead. In such a semiconductor device, a gate electrode pad is arranged at a position close to lead posts of the gate lead and the source lead and a source electrode pad is arranged at a position far from the lead posts of the gate lead and the source lead.